L Number	Hits	Search Text	DB	Time stamp
1	6910	438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.	USPAT; US-PGPUB	2004/11/08 14:55
2	1918	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and (aerosol spray$6 nanoparticle)	USPAT; US-PGPUB	2004/11/08 14:56
3	27	(438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls.) and (427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.)	USPAT; US-PGPUB	2004/11/08 14:59
4	88	((aerosol spray$6 nanoparticle) with (conduct$6 copper cu silver ag gold au) with (via hole opening plug seed)) same (integrated semiconductor memory cell)	USPAT; US-PGPUB	2004/11/08 15:04
5	10	5529634.URPN.	USPAT	2004/11/08 15:11
6	156	((aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au) same (via hole opening plug seed)) and (integrated semiconductor memory cell)	EPO; JPO; DERWENT; IBM_TDB	2004/11/08 15:12
7	95	((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and ((aerosol spray$6 nanoparticle) same (conduct$6 copper cu silver ag gold au))) and (((integrated adj circuit) ic semiconductor memory cell) same (via hole opening plug seed))	USPAT; US-PGPUB	2004/11/08 15:49
8	111	((maskless adj mesoscale adj2 (materials deposition)) m3d "m.sup.3d" "m.sup.3 d") and (via plug semiconductor ic (integrated adj circuit)) and (conduct$6 copper cu silver ag gold au)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:03
9	10	(memory adj (cell circuit array)) same (column with row with (decoder address)) same (sensing adj (circuit amplifier)) same (via plug)	USPAT; US-PGPUB	2004/11/08 16:20
10	2	((memory adj (cell circuit array)) same (column with row with (decoder address)) same (sensing adj (circuit amplifier))) and (plug same ((bit adj line) (word adj line) wordline bitline))	USPAT; US-PGPUB	2004/11/08 16:21
11	9	((memory adj (cell circuit array)) same (column with row with (decoder address)) same (sensing adj (circuit amplifier))) and (interconnect$6 same ((bit adj line) (word adj line) wordline bitline))	USPAT; US-PGPUB	2004/11/08 16:22
12	638	((438/637.ccls. 438/641.ccls. 438/667.ccls. 438/675.ccls. 438/678.ccls. 438/686.ccls. 427/97.ccls. 427/110.ccls. 427/125.ccls. 427/191.ccls. 427/192.ccls. 427/236.ccls. 427/383.1.ccls. 427/422.ccls. 427/455.ccls. 427/597.ccls.) and (aerosol spray$6 nanoparticle)) and (integrated semiconductor memory cell)	USPAT; US-PGPUB	2004/11/08 16:28